

NEW CLAIMS: DISCUSSION

New claims 70-78 are added in this response.

New claim 70 recites a method for patterning pillars, the method comprising: a) projecting light onto photoresist using a photomask, the photomask comprising: a plurality of transmitting nonprinting windows transmitting light in a first phase; a transmitting area transmitting light in a second phase, each transmitting window of the plurality substantially entirely surrounded by and in contact with the transmitting area with no blocking material intervening, wherein the second phase is substantially opposite the first phase, and wherein a first width of unbroken transmitting area surrounds each transmitting window of the plurality on all sides, the first width sufficient for the unbroken transmitting area to print when the photomask is used to expose photoresist; and b) developing the photoresist to form a plurality of photoresist features, wherein the photoresist features of the plurality are photoresist pillars.

Support for this claim can be found, for example, in paragraphs [0064], [0067], and [0094]. Support for claims 71 and 72, which recite the first and second phase, appears, for example, in paragraph [0063] and Fig. 10a. Support for claim 73 and 74, which recites dimensions of the transmitting windows, is found, for example, at paragraph [0085]. Support for claim 75, which recites that the windows are rectangular, can be found, *inter alia*, at paragraphs [0072] and [0088] and in Figs. 10a and 15.

Claim 76 recites the method of claim 70 further comprising etching to form a plurality of patterned pillars from the photoresist pillars. Claim 77 adds to claim 76 the limitation that each claim of the plurality comprises polysilicon, while claim 78 adds to claim 76 the limitation that each of the plurality of patterned pillars is a portion of a memory cell. Support for these claim

can be found in paragraphs [0092] to [0095]. None of these claim amendments constitutes new matter.